

-20V P-Channel MOSFET

MOSFET Product Summary

V_{DS}	$R_{DS(ON)}(Typ.)$	I_D
-20V	21mΩ @ $V_{GS}=-4.5V$	-7A
	28mΩ @ $V_{GS}=-2.5V$	

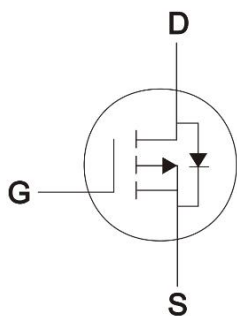
Description

The PM2305BL3 uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT23-3L, which accord with the RoHS standard and Halogen Free standard.

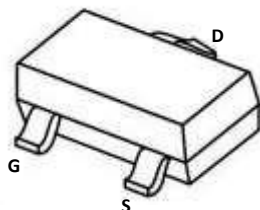
Features

- Low Gate Charge and $R_{DS(ON)}$
- Lead free product is acquired
- High Power and current handing capability

Dimensions and Pin Configuration



Circuit diagram



SOT23-3L

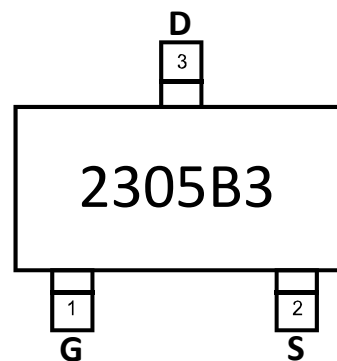
Mechanical Characteristics

- Package: SOT23-3L
- Case Material: "Green" Molding Compound
- Marking Information: See Below

Applications

- DC-DC converter
- Apply for high-frequency switching and synchronous rectification

Marking Information



2305B3 = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PM2305BL3	3000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-7	A

Pulsed Drain Current _(note1)	I_{DM}	-24.8	A
Power Dissipation	P_D	1.6	W
Thermal Resistance from Junction to Ambient _(note1)	$R_{\theta JA}$	80	°C/W
Junction Temperature	T_J	-55~ +150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

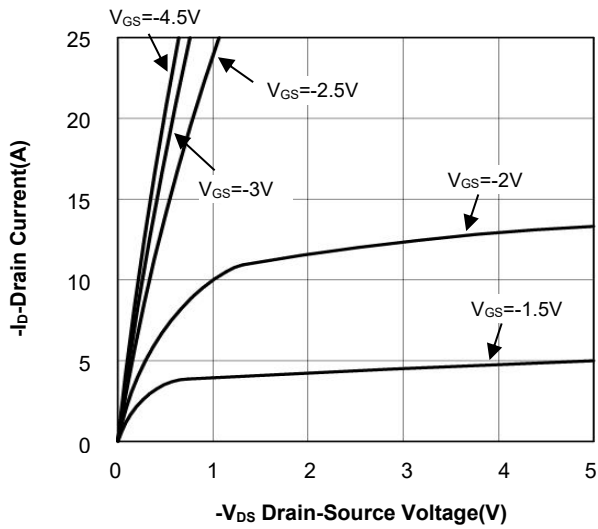
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =-250μA	-20	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V	-	-	-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.6	-1.0	V
Drain-source on-resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-5A	-	21	30	mΩ
		V _{GS} =-2.5V, I _D =-4A	-	28	35	
Diode Forward voltage _(note1)	V _{SD}	I _S =-5A,V _{GS} = 0V	-	-	-1	V
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V,f=1MHz	-	1493	-	pF
Output Capacitance	C _{oss}		-	176	-	
Reverse Transfer Capacitance	C _{rss}		-	130	-	
Switching Characteristics						
Turn-on delay time	t _{d(on)}	V _{GS} =-4.5V, V _{DS} =-10V, R _L =1.5Ω, R _{GEN} =6Ω	-	13	-	nS
Turn-on rise time	t _r		-	32	-	
Turn-off delay time	t _{d(off)}		-	27	-	
Turn-off fall time	t _f		-	9	-	
Total Gate Charge	Q _g	V _{GS} =-4.5V,V _{DS} =-10V,I _D =-5A		14.2		nC
Gate Source Charge	Q _{gs}			1.1		
Gate Drain Charge	Q _{gd}			4.8		

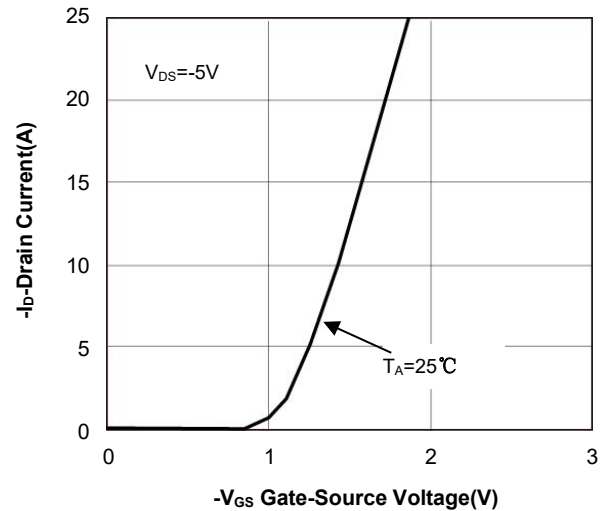
Notes:

1. Repetitive rating; pulse width limited by maximum junction temperature.
2. EAS condition: $T_J = 25^{\circ}\text{C}, V_{DD} = -20V, V_G = 10V, R_g = 25\Omega, L = 0.5mH$.

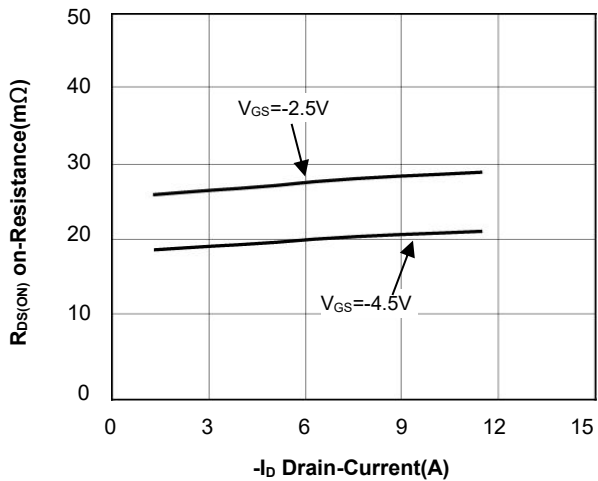
Typical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)



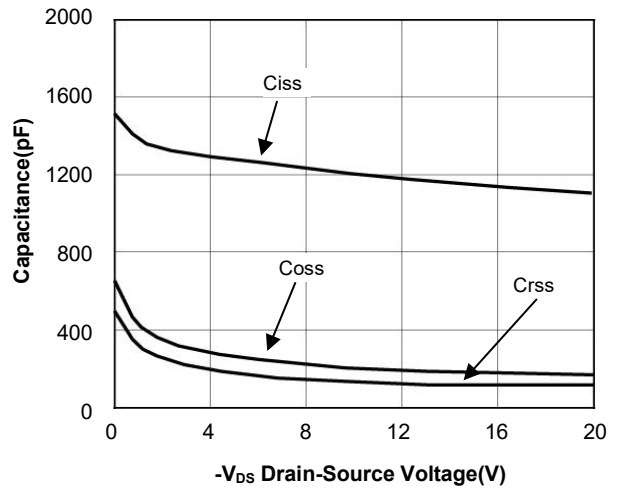
Drain Current vs. Drain-Source Voltage



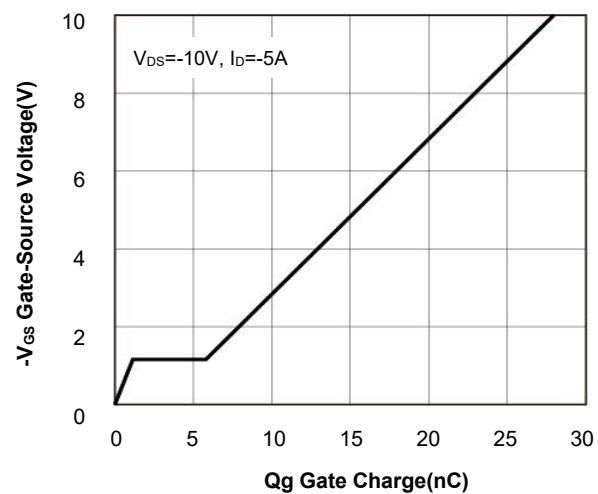
Drain Current vs. Gate-Source Voltage



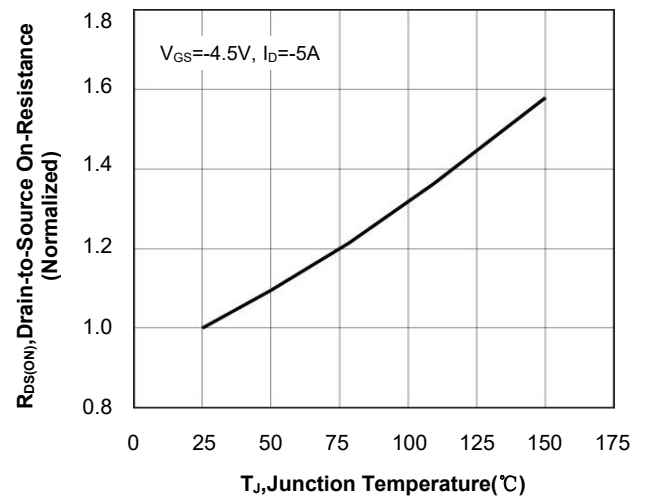
$R_{DS(ON)}$ On-Resistance vs. Drain-Current



Capacitance vs. Drain-Source Voltage

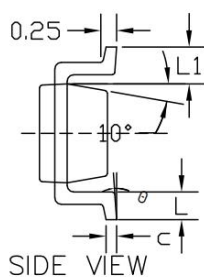
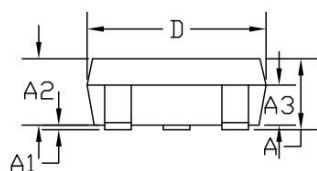
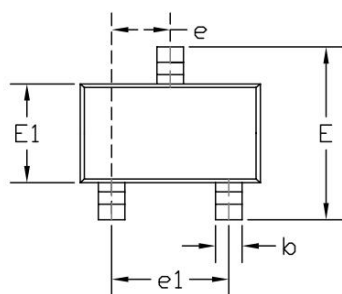


Drain Current vs. Drain-Source Voltage



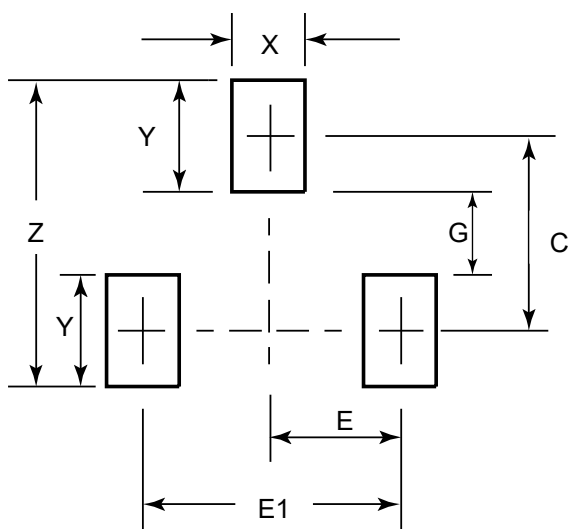
Normalized On-Resistance vs. Temperature

SOT23-3L Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	1.05	1.15	1.25
A1	0.01	0.06	0.11
A2	1.00	1.10	1.20
A3	0.60	0.65	0.70
b	0.35	0.40	0.45
c	0.12	0.15	0.18
D	2.82	2.92	3.02
E	2.65	2.80	2.95
E1	1.50	1.60	1.70
L	0.30	-	0.50
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
θ	0°	4°	8°
L1	0.6REF		

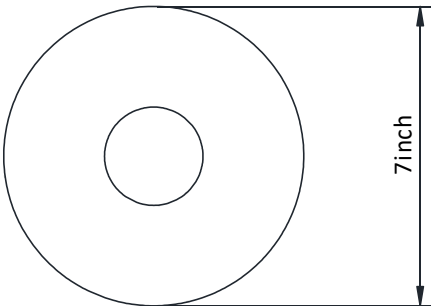
Suggested Land Pattern



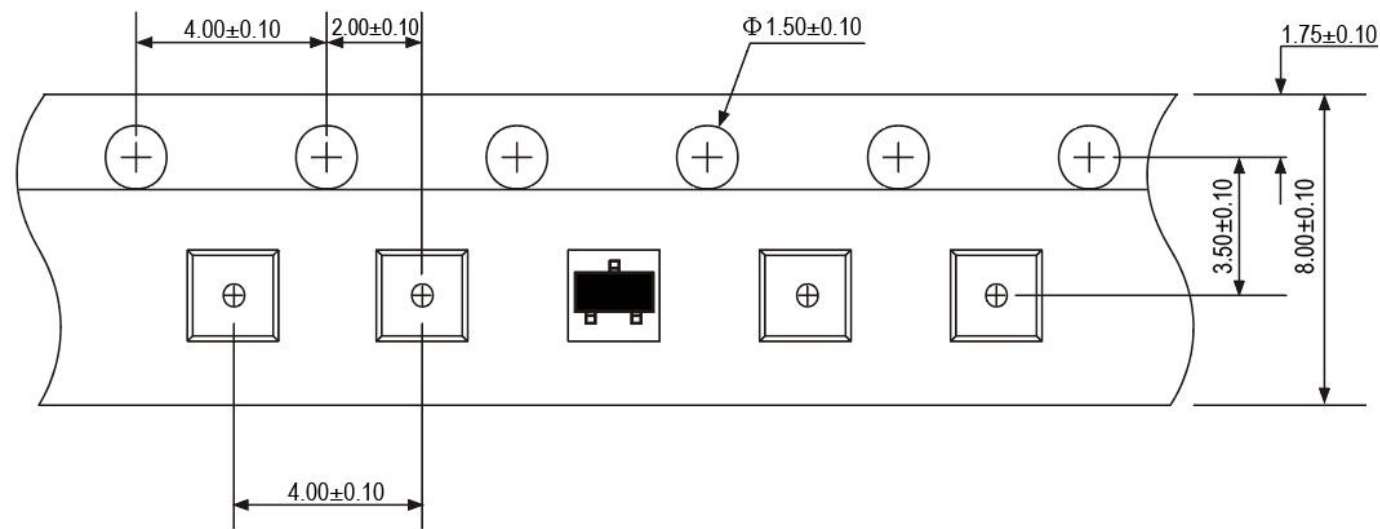
SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.40	0.094
E	0.95	0.037
E1	1.90	0.075
G	1.40	0.055
X	0.80	0.031
Y	1.00	0.039
Z	3.40	0.134

TAPE AND REEL INFORMATION

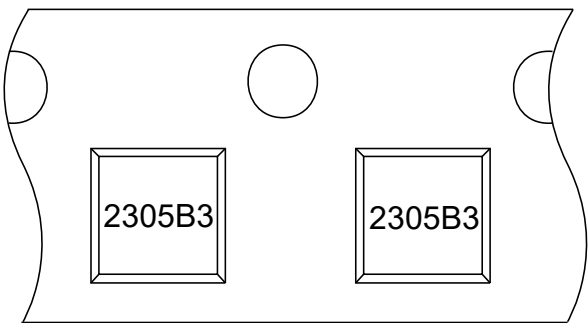
Reel Dimensions



Tape Dimensions



Unit:mm



User Direction of Feed

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